

## N-Channel 30-V (D-S) MOSFET

### PRODUCT SUMMARY

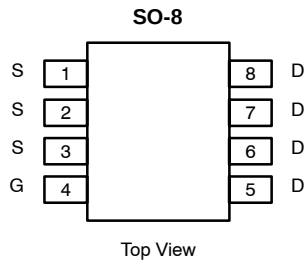
| $V_{DS}$ (V) | $r_{DS(on)}$ ( $\Omega$ ) | $I_D$ (A) | $Q_g$ (Typ) |
|--------------|---------------------------|-----------|-------------|
| 30           | 0.00325 @ $V_{GS} = 10$ V | 25        | 36          |
|              | 0.0042 @ $V_{GS} = 4.5$ V | 22        |             |

### FEATURES

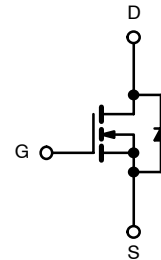
- Ultra Low On-Resistance Using High Density TrenchFET® Gen II Power MOSFET Technology
- $Q_g$  Optimized
- 100%  $R_g$  Tested

### APPLICATIONS

- Synchronous Buck Low-Side
  - Notebook
  - Server
  - Workstation
- Synchronous Rectifier, POL



Ordering Information: Si4336DY  
Si4336DY-T1 (with Tape and Reel)



N-Channel MOSFET

### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

| Parameter                                                             |                            | Symbol         | 10 secs    | Steady State | Unit               |
|-----------------------------------------------------------------------|----------------------------|----------------|------------|--------------|--------------------|
| Drain-Source Voltage                                                  |                            | $V_{DS}$       | 30         |              | V                  |
| Gate-Source Voltage                                                   |                            | $V_{GS}$       | $\pm 20$   |              |                    |
| Continuous Drain Current ( $T_J = 150^{\circ}\text{C}$ ) <sup>a</sup> | $T_A = 25^{\circ}\text{C}$ | $I_D$          | 25         | 17           | A                  |
|                                                                       | $T_A = 70^{\circ}\text{C}$ |                | 20         | 13           |                    |
| Pulsed Drain Current (10 $\mu\text{s}$ Pulse Width)                   |                            | $I_{DM}$       | 70         |              |                    |
| Continuous Source Current (Diode Conduction) <sup>a</sup>             |                            | $I_S$          | 2.9        | 1.3          |                    |
| Avalanche Current                                                     | L = 0.1 mH                 | $I_{AS}$       | 50         |              | W                  |
| Maximum Power Dissipation <sup>a</sup>                                | $T_A = 25^{\circ}\text{C}$ | $P_D$          | 3.5        | 1.6          |                    |
|                                                                       | $T_A = 70^{\circ}\text{C}$ |                | 2.2        | 1            |                    |
| Operating Junction and Storage Temperature Range                      |                            | $T_J, T_{stg}$ | -55 to 150 |              | $^{\circ}\text{C}$ |

### THERMAL RESISTANCE RATINGS

| Parameter                                |                 | Symbol     | Typical | Maximum | Unit               |
|------------------------------------------|-----------------|------------|---------|---------|--------------------|
| Maximum Junction-to-Ambient <sup>a</sup> | $t \leq 10$ sec | $R_{thJA}$ | 29      | 35      | $^\circ\text{C/W}$ |
|                                          | Steady State    |            | 67      | 80      |                    |
| Maximum Junction-to-Foot (Drain)         | Steady State    | $R_{thJF}$ | 13      | 16      |                    |

#### Notes

a. Surface Mounted on 1" x 1" FR4 Board.

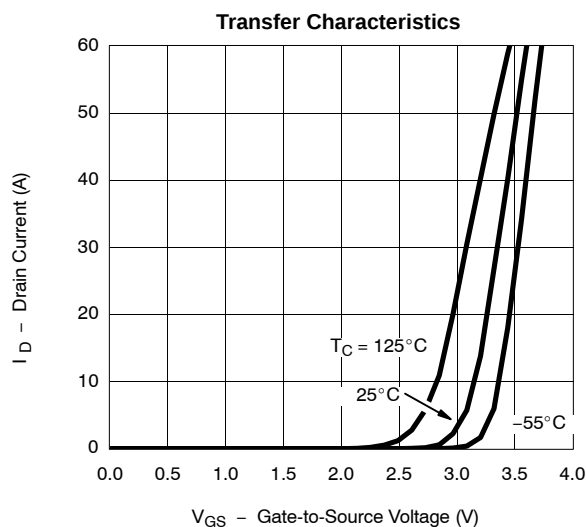
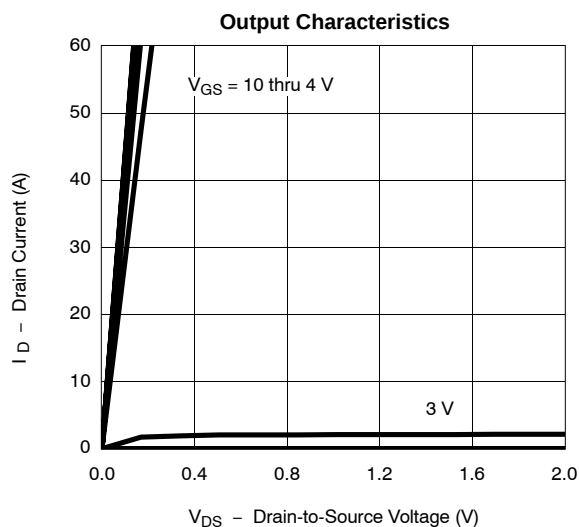
**SPECIFICATIONS ( $T_J = 25^\circ\text{C}$  UNLESS OTHERWISE NOTED)**

| Parameter                                     | Symbol       | Test Condition                                                                                                         | Min | Typ    | Max       | Unit          |
|-----------------------------------------------|--------------|------------------------------------------------------------------------------------------------------------------------|-----|--------|-----------|---------------|
| <b>Static</b>                                 |              |                                                                                                                        |     |        |           |               |
| Gate Threshold Voltage                        | $V_{GS(th)}$ | $V_{DS} = V_{GS}$ , $I_D = 250\ \mu\text{A}$                                                                           | 1.0 |        | 3.0       | V             |
| Gate-Body Leakage                             | $I_{GSS}$    | $V_{DS} = 0\ \text{V}$ , $V_{GS} = \pm 20\ \text{V}$                                                                   |     |        | $\pm 100$ | nA            |
| Zero Gate Voltage Drain Current               | $I_{DSS}$    | $V_{DS} = 30\ \text{V}$ , $V_{GS} = 0\ \text{V}$                                                                       |     |        | 1         | $\mu\text{A}$ |
|                                               |              | $V_{DS} = 30\ \text{V}$ , $V_{GS} = 0\ \text{V}$ , $T_J = 55^\circ\text{C}$                                            |     |        | 5         |               |
| On-State Drain Current <sup>a</sup>           | $I_{D(on)}$  | $V_{DS} \geq 5\ \text{V}$ , $V_{GS} = 10\ \text{V}$                                                                    | 30  |        |           | A             |
| Drain-Source On-State Resistance <sup>a</sup> | $r_{DS(on)}$ | $V_{GS} = 10\ \text{V}$ , $I_D = 25\ \text{A}$                                                                         |     | 0.0026 | 0.00325   | $\Omega$      |
|                                               |              | $V_{GS} = 4.5\ \text{V}$ , $I_D = 22\ \text{A}$                                                                        |     | 0.0033 | 0.0042    |               |
| Forward Transconductance <sup>a</sup>         | $g_{fs}$     | $V_{DS} = 15\ \text{V}$ , $I_D = 25\ \text{A}$                                                                         |     | 110    |           | S             |
| Diode Forward Voltage <sup>a</sup>            | $V_{SD}$     | $I_S = 2.9\ \text{A}$ , $V_{GS} = 0\ \text{V}$                                                                         |     | 0.72   | 1.1       | V             |
| <b>Dynamic<sup>b</sup></b>                    |              |                                                                                                                        |     |        |           |               |
| Input Capacitance                             | $C_{iss}$    | $V_{DS} = 15\ \text{V}$ , $V_{GS} = 0\ \text{V}$ , $f = 1\ \text{MHz}$                                                 |     | 5600   |           | pF            |
| Output Capacitance                            | $C_{oss}$    |                                                                                                                        |     | 860    |           |               |
| Reverse Transfer Capacitance                  | $C_{rss}$    |                                                                                                                        |     | 415    |           |               |
| Total Gate Charge                             | $Q_g$        | $V_{DS} = 15\ \text{V}$ , $V_{GS} = 4.5\ \text{V}$ , $I_D = 20\ \text{A}$                                              |     | 36     | 50        | nC            |
| Gate-Source Charge                            | $Q_{gs}$     |                                                                                                                        |     | 18     |           |               |
| Gate-Drain Charge                             | $Q_{gd}$     |                                                                                                                        |     | 10     |           |               |
| Gate Resistance                               | $R_g$        |                                                                                                                        | 0.8 | 1.3    | 2.0       | $\Omega$      |
| Turn-On Delay Time                            | $t_{d(on)}$  | $V_{DD} = 15\ \text{V}$ , $R_L = 15\ \Omega$<br>$I_D \cong 1\ \text{A}$ , $V_{GEN} = 10\ \text{V}$ , $R_g = 6\ \Omega$ |     | 24     | 35        | ns            |
| Rise Time                                     | $t_r$        |                                                                                                                        |     | 16     | 25        |               |
| Turn-Off Delay Time                           | $t_{d(off)}$ |                                                                                                                        |     | 90     | 140       |               |
| Fall Time                                     | $t_f$        |                                                                                                                        |     | 32     | 50        |               |
| Source-Drain Reverse Recovery Time            | $t_{rr}$     | $I_F = 2.9\ \text{A}$ , $di/dt = 100\ \text{A}/\mu\text{s}$                                                            |     | 45     | 70        |               |

## Notes

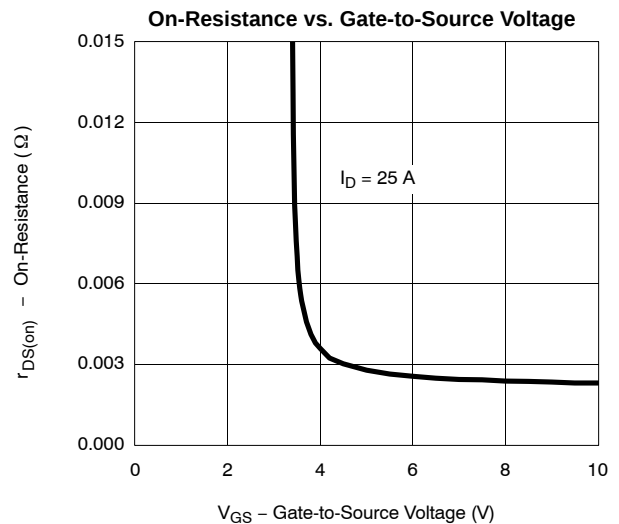
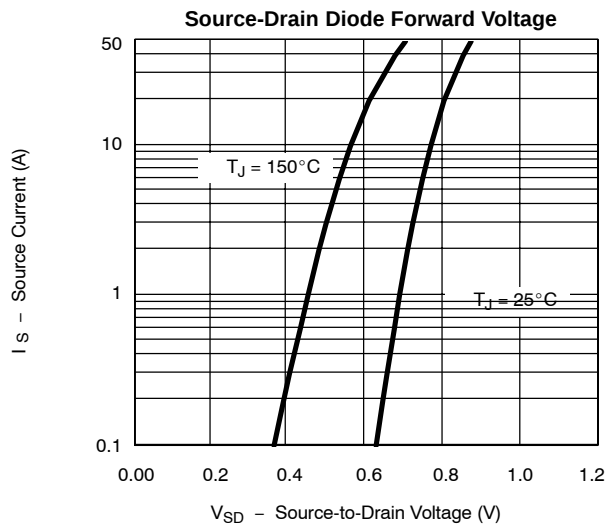
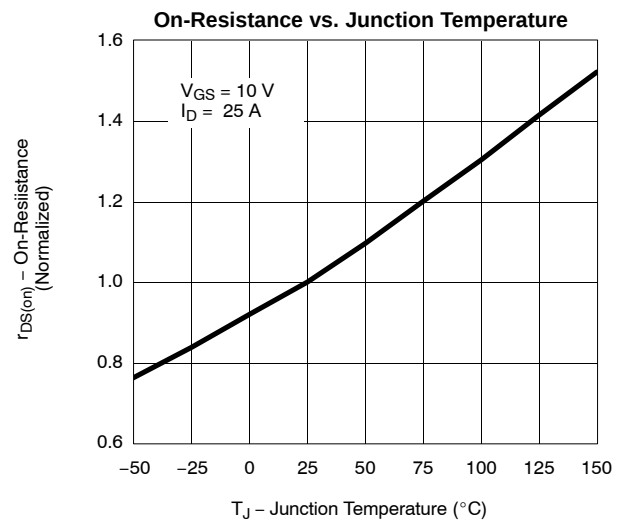
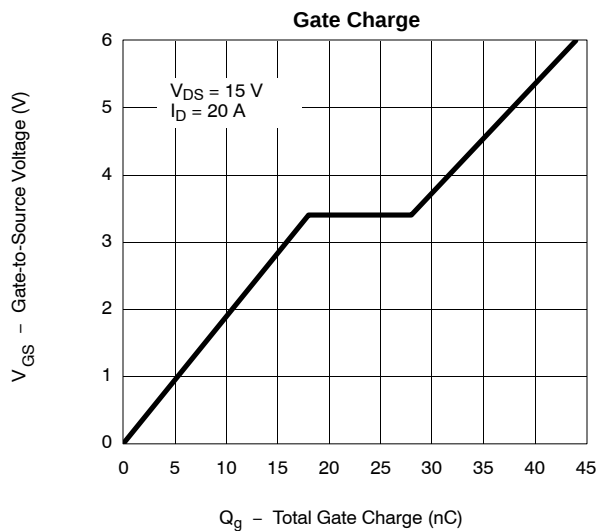
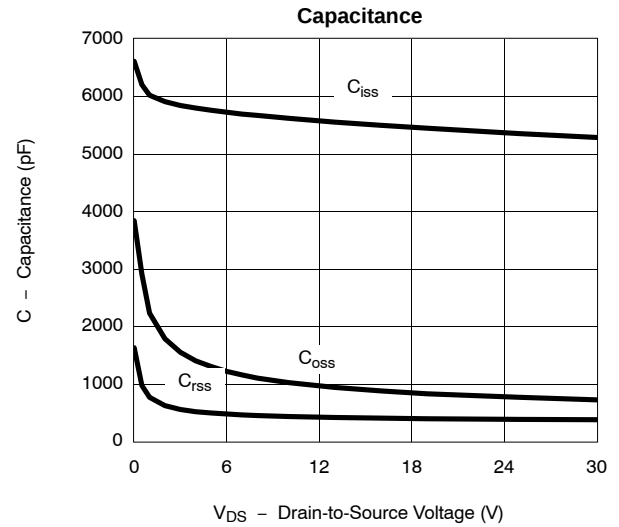
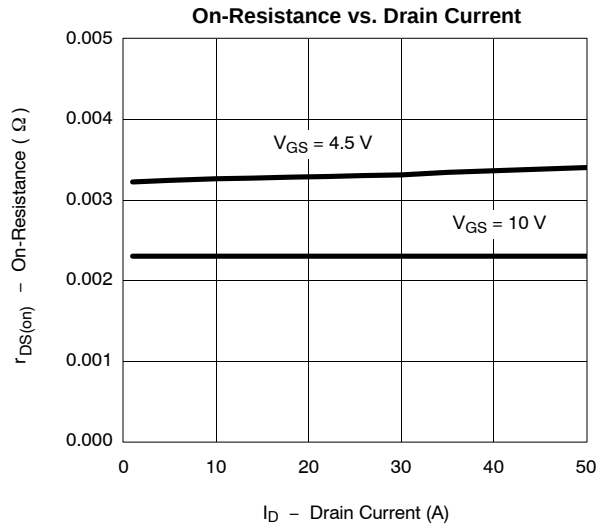
- a. Pulse test; pulse width  $\leq 300\ \mu\text{s}$ , duty cycle  $\leq 2\%$ .  
b. Guaranteed by design, not subject to production testing.

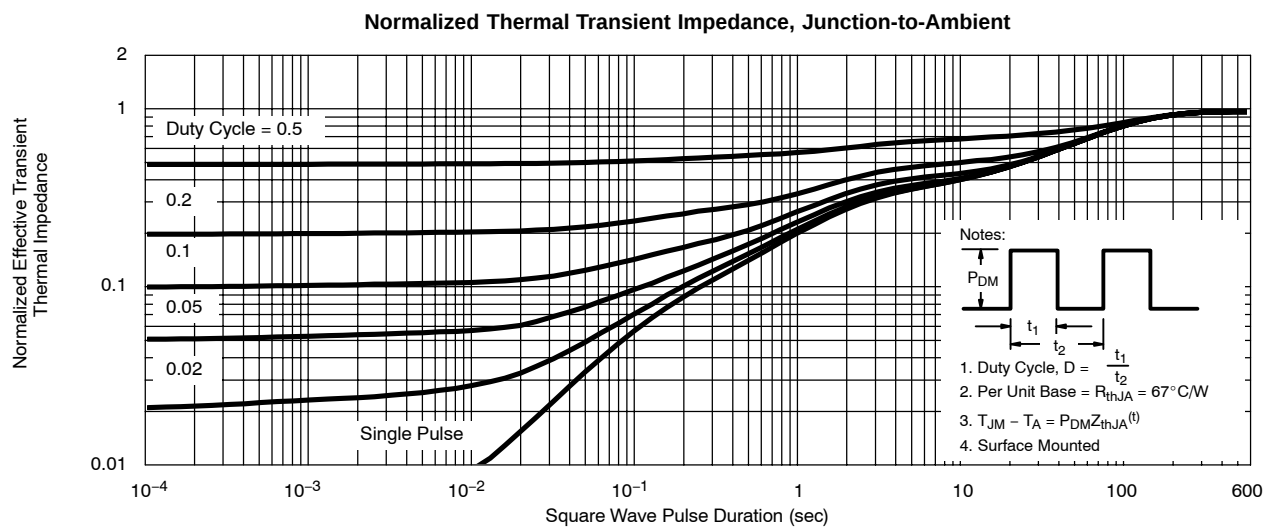
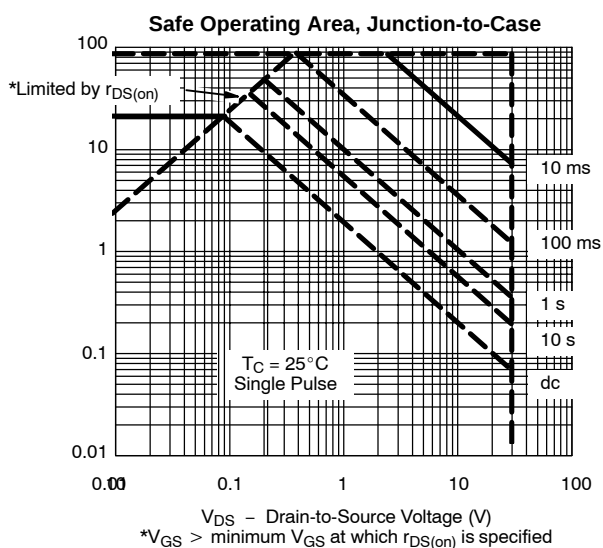
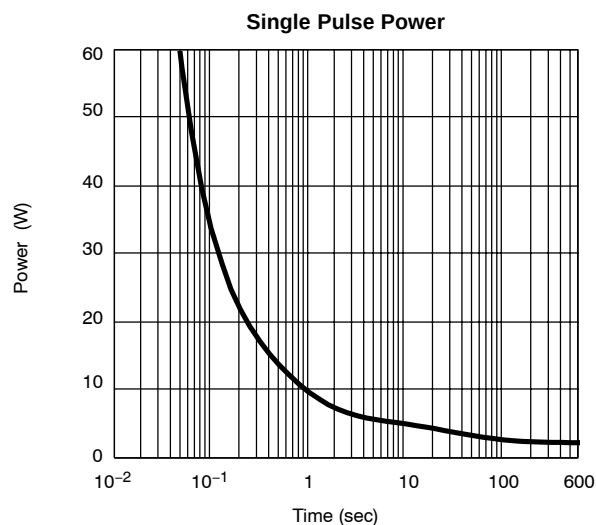
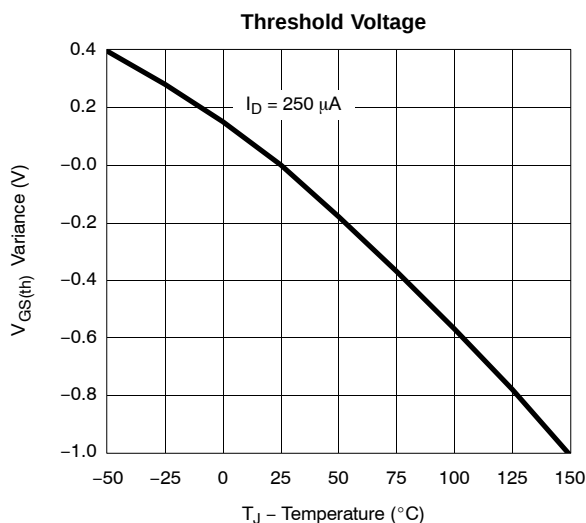
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS ( $25^\circ\text{C}$  UNLESS NOTED)**



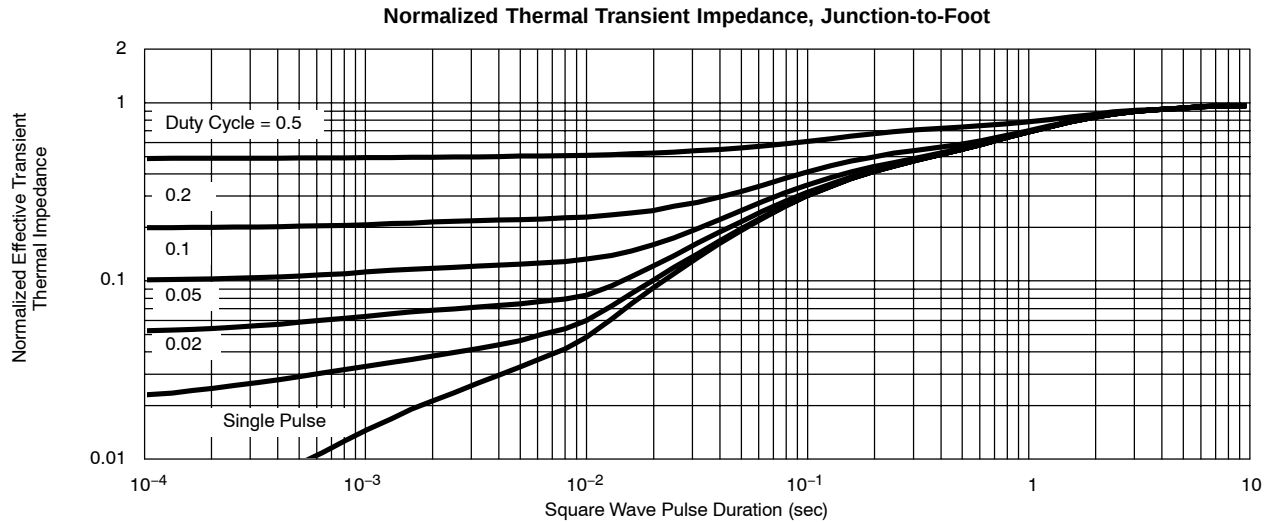
**TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)**



**TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)**




**TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)**



Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <http://www.vishay.com/ppg?72417>.